

5DS02M

Switching Diode

PHENITEC
SEMICONDUCTOR

Features

- High-speed

Item	Characteristics
Wafer size	5 inch
Chip size	260*260um

Maximum Ratings @25degC

Item	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V _{RSM}	105	V
Repetitive Peak Reverse Voltage	V _{RRM}	100	V
Repetitive Peak Forward Current	I _{FRM}	300	mA
Continuous Forward Current	I _O	100	mA
Non-Repetitive Peak Forward Current @t=1us	I _{FSM}	2.0	A
Power Dissipation	P _D	200	mW
Junction Temperature	T _j	150	degC
Storage Temperature	T _{stg}	-55to+150	degC

Electrical Characteristics @25degC

Item	Symbol	Min	Max	Unit	Test Condition
Forward Voltage	V _F		1.2	V	I _F =100mA
Breakdown Voltage	V _B	105		V	I _R =100uA
Reverse Current	I _R		25.0	nA	V _R =30V
			10.0	uA	V _R =100V
Capacitance	C _T		2.0	pF	V _R =0V, f=1MHz
Reverse Recovery Time	t _{rr}		4.0	nsec	I _F =-I _R =10mA R _L =100Ω, i _{rr} =1mA

Wafer Probing Spec @25degC

Symbol	Min	Max	Unit	Test Condition
V _F		1.14	V	I _F =100mA
V _B	105		V	I _R =100uA
I _{R1}		25.0	nA	V _R =30V
I _{R2}		10.0	uA	V _R =100V

Ordering Information

Chip Type	Chip Thickness	Back Metalization
5DS02MH	230±15um	Au/As-Au (For AgEpoxy/Eutectic)

Note

Equivalent type : BAW62

SheetNo.

Rev.